

# International **IOR** Rectifier

Bulletin I0125J 07/97

## IR180LM..CS05CB SERIES

### FAST RECOVERY DIODES

- Junction Size: Square 180 mils
- Wafer Size: 4"
- $V_{RRM}$  Class: 1000 and 1200 V
- Passivation Process: Glassivated MOAT
- Reference IR Packaged Part: 20ETF Series

### Major Ratings and Characteristics

Parameters	Units	Test Conditions
$V_{FM}$ Maximum Forward Voltage	1350mV	$T_J = 25^\circ\text{C}$ , $I_F = 20\text{ A}$
$V_{RRM}$ Reverse Breakdown Voltage Range	1000 and 1200 V	$T_J = 25^\circ\text{C}$ , $I_{RRM} = 100\text{ }\mu\text{A}$ (1)

(1) Nitrogen flow on die edge.

### Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 $\mu\text{m}$ )
Chip Dimensions	180 x 180 mils (4.57x4.57 mm) - see drawing
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	260 $\mu\text{m}$
Maximum Width of Sawing Line	45 $\mu\text{m}$
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

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**IR** Rectifier

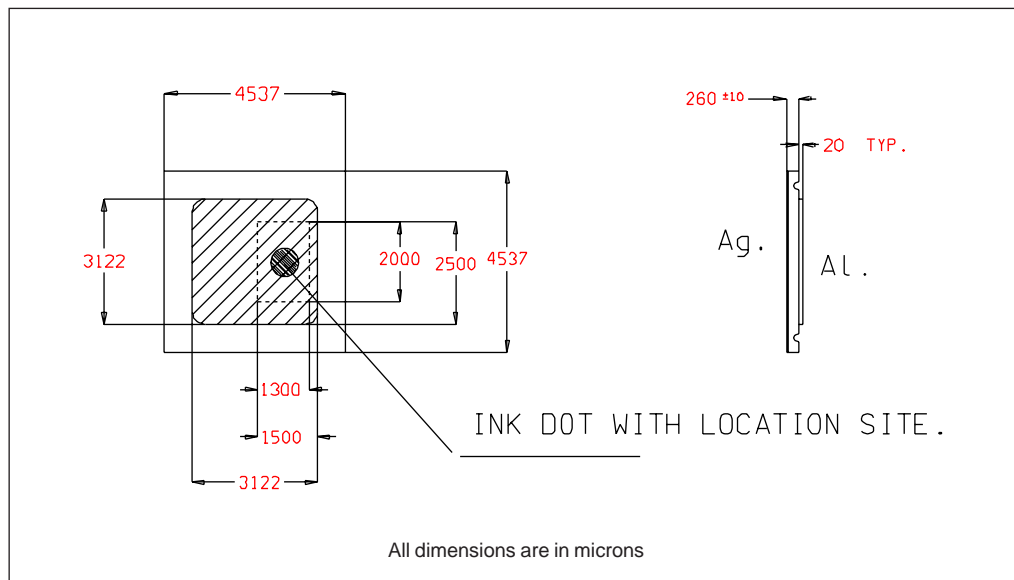
## Ordering Information Table

Device Code							
IR	180	L	M	12	C	S05	CB
①	②	③	④	⑤	⑥	⑦	⑧
1	- International Rectifier Device						
2	- Chip Dimension in Mils						
3	- Type of Device: L = Wire Bondable Fast Recovery Diode						
4	- Passivation Process: M = Glassivated MOAT						
5	- Voltage code: Code x 100 = $V_{RRM}$						
6	- Metallization: C = Aluminium (Anode) - Silver (Cathode)						
7	- Fast Recovery Type: S05 = 500 nsec						
8	- CB = Probed Uncut Die (wafer in box) None = Probed Die in chip carrier						

### Available Class

10 = 1000 V  
12 = 1200 V

## Outline Table



## Wafer Layout

